

AMENDMENTS TO THE SPECIFICATION:

Page 14, replace the paragraph beginning on line 24 and bridging pages 14 and 15 with the following amended paragraph:

--In Fig. 4, a first SiCN film 102 is formed as a barrier insulating film on an insulating film [[201]] 101 formed on a semiconductor substrate that includes transistors. An interlayer insulating film 103, which is the ladder type hydrogenated polysiloxane film, is formed on the first SiCN film 102. A SiO₂ film 104 is formed on the interlayer insulating film 103. The trenches for the interconnections are formed through the first SiCN film 102, the interlayer insulating film 103 and the SiO₂ film 104. A modified insulating film 105 is formed in the side wall of the trench in the interlayer insulating film 103.--